



High-end Power Semiconductor Manufacturer

# ZP1250A 1000-1800V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current		$I_{FAV}$		1250 A	
Repetitive peak reverse voltage		$V_{RRM}$		1000 – 1800 V	
$V_{RRM}$ , V	1000	1200	1400	1600	1800
Voltage code	10	12	14	16	18
$T_j$ , °C			-60 – 190		

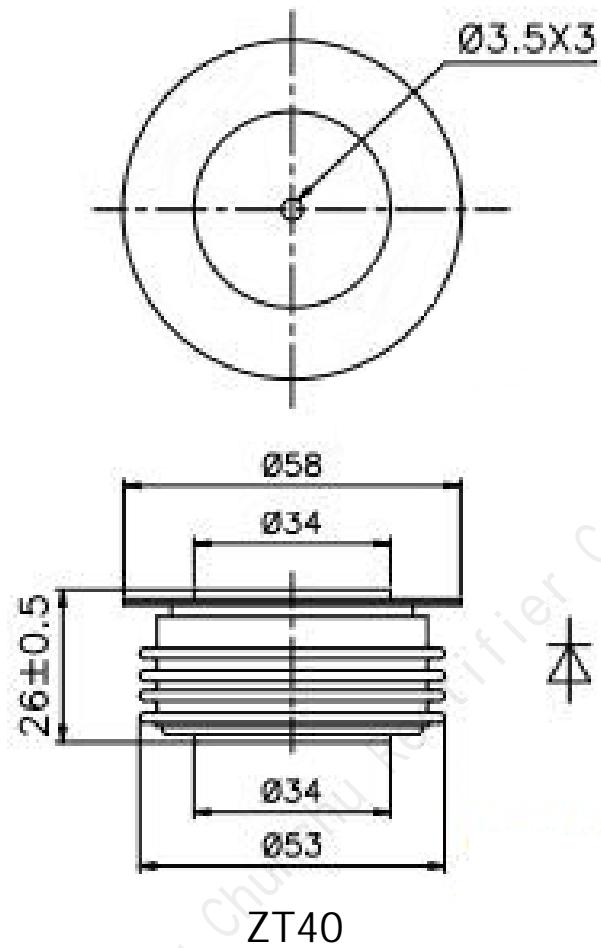
## MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
<b>ON-STATE</b>					
$I_{FAV}$	Average forward current	A	1250	$T_c=100$ °C; Double side cooled; 180° half-sine wave; 50 Hz	
$I_{FRMS}$	RMS forward current	A	1963	$T_c=114$ °C; Double side cooled; 180° half-sine wave; 50 Hz	
$I_{FSM}$	Surge forward current	kA	20.0	$T_j=T_{j \max}$	180° half-sine wave; 50 Hz ( $t_p=10$ ms); single pulse; $V_R=0$ V;
			23.0	$T_j=25$ °C	180° half-sine wave; 60 Hz ( $t_p=8.3$ ms); single pulse; $V_R=0$ V;
$I^2t$	Safety factor	$A^2s \cdot 10^3$	2000	$T_j=T_{j \max}$	180° half-sine wave; 50 Hz ( $t_p=10$ ms); single pulse; $V_R=0$ V;
			2645	$T_j=25$ °C	180° half-sine wave; 60 Hz ( $t_p=8.3$ ms); single pulse; $V_R=0$ V;
<b>BLOCKING</b>					
$V_{RRM}$	Repetitive peak reverse voltages	V	1000–1800	$T_{j \min} < T_j < T_{j \max}$ ; 180° half-sine wave; 50 Hz;	
$V_{RSM}$	Non-repetitive peak reverse voltages	V	1100–1900	$T_{j \min} < T_j < T_{j \max}$ ; 180° half-sine wave; 50 Hz;single pulse;	
$V_R$	Reverse continuous voltages	V	$0.75 \cdot V_{RRM}$	$T_j=T_{j \max}$ ;	
<b>THERMAL</b>					
$T_{stg}$	Storage temperature	°C	-60–190		
$T_j$	Operating junction temperature	°C	-60–190		
<b>MECHANICAL</b>					
F	Mounting force	kN	14.0–16.0		
a	Acceleration	$m/s^2$	50 100	Device unclamped Device clamped	

## CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
<b>ON-STATE</b>					
V <sub>FM</sub>	Peak forward voltage, max	V	1.66	T <sub>j</sub> =25 °C; I <sub>FM</sub> =3925 A	
V <sub>F(TO)</sub>	Forward threshold voltage, max	V	0.97	T <sub>j</sub> =T <sub>j max</sub> ; 0.5 π I <sub>FAV</sub> < I <sub>T</sub> < 1.5 π I <sub>FAV</sub>	
r <sub>T</sub>	Forward slope resistance, max	mΩ	0.260		
<b>BLOCKING</b>					
I <sub>RRM</sub>	Repetitive peak reverse current, max	mA	70	T <sub>j</sub> =T <sub>j max</sub> ; V <sub>R</sub> =V <sub>RRM</sub>	
<b>THERMAL</b>					
R <sub>thjc</sub>	Thermal resistance, junction to case, max	°C/W	0.035	Direct current	Double side cooled
R <sub>thjc-A</sub>			0.077		Anode side cooled
R <sub>thjc-K</sub>			0.063		Cathode side cooled
R <sub>thck</sub>	Thermal resistance, case to heatsink, max	°C/W	0.006	Direct current	
<b>MECHANICAL</b>					
w	Weight, typ	g	280		
D <sub>s</sub>	Surface creepage distance	mm (inch)	33.30 (1.311)		
D <sub>a</sub>	Air strike distance	mm (inch)	22.50 (0.886)		

## OVERALL DIMENSIONS



All dimensions in millimeters